五、中文發明摘要

發明名稱:極紫外光 EUV 用光阻組成物及光阻圖型 之形成方法

本發明之光阻組成物,爲含有(A1)下述式(I)所示多元酚化合物(a)中之酚性羥基中一部份或全部被酸解離性溶解抑制基所保護之保護體,與(B)經由曝光產生酸之酸產生劑成份之 EUV 用光阻組成物。 [化 1]

六、英文發明摘要

發明名稱:

RESIST COMPOSITION FOR EUVAND PROCESS FOR FORMING RESIST PATTERN

The resist composition of the present invention is a resist composition for the use of EUV including (A1) a protected body in which a part or all of phenolic hydroxy group in a polyphenol compound (a) represented by the following general formula (I):

is protected by an acid dissociative dissolution inhibiting agent and (B) an acid generating agent component which generates an acid by exposure.